

Title (en)
Stiffening layers for the relaxation of strained layers

Title (de)
Versteifungsschichten zur Relaxation von verspannten Schichten

Title (fr)
Couches de durcissement pour le relâchement de couches contraintes

Publication
EP 2159836 A1 20100303 (EN)

Application
EP 08290797 A 20080825

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Abstract (en)
The present invention relates to a method for relaxing a strained material layer, comprising providing a strained material layer and a low-viscosity layer formed on a first face of the strained material layer; forming a stiffening layer on at least one part of a second face of the strained material layer opposite to the first face thereby forming a multilayer stack; and subjecting the multilayer stack to a heat treatment thereby at least partially relaxing the strained material layer.

IPC 8 full level
H01L 21/84 (2006.01); **H01L 21/20** (2006.01)

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H01L 21/20 (2013.01 - KR); **H01L 21/324** (2013.01 - KR); **H01L 21/84** (2013.01 - EP US)

Citation (search report)
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